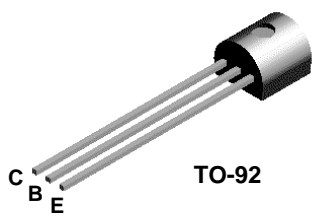
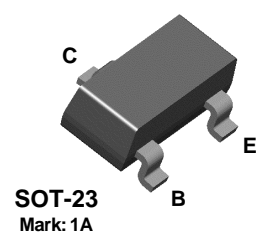


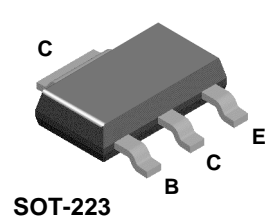
## 2N3904



## MMBT3904



## PZT3904



### NPN General Purpose Amplifier

This device is designed as a general purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.

#### Absolute Maximum Ratings\* T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		2N3904	*MMBT3904	**PZT3904	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625	350	1,000	mW
		5.0	2.8	8.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3			°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

\* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

# NPN General Purpose Amplifier

(continued)

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
<b>OFF CHARACTERISTICS</b>					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1.0\text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6.0		V
$I_{BL}$	Base Cutoff Current	$V_{CE} = 30\text{ V}, V_{EB} = 3\text{ V}$		50	nA
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 30\text{ V}, V_{EB} = 3\text{ V}$		50	nA

## ON CHARACTERISTICS\*

$h_{FE}$	DC Current Gain	$I_C = 0.1\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 1.0\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 50\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	40 70 100 60 30	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 50\text{ mA}, I_B = 5.0\text{ mA}$		0.2 0.3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 50\text{ mA}, I_B = 5.0\text{ mA}$	0.65	0.85 0.95	V V

## SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 10\text{ mA}, V_{CE} = 20\text{ V}, f = 100\text{ MHz}$	300		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 5.0\text{ V}, I_E = 0, f = 1.0\text{ MHz}$		4.0	pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 1.0\text{ MHz}$		8.0	pF
NF	Noise Figure	$I_C = 100\text{ }\mu\text{A}, V_{CE} = 5.0\text{ V}, R_S = 1.0\text{ k}\Omega, f = 10\text{ Hz to }15.7\text{ kHz}$		5.0	dB

## SWITCHING CHARACTERISTICS

$t_d$	Delay Time	$V_{CC} = 3.0\text{ V}, V_{BE} = 0.5\text{ V},$		35	ns
$t_r$	Rise Time	$I_C = 10\text{ mA}, I_{B1} = 1.0\text{ mA}$		35	ns
$t_s$	Storage Time	$V_{CC} = 3.0\text{ V}, I_C = 10\text{ mA}$		200	ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 1.0\text{ mA}$		50	ns

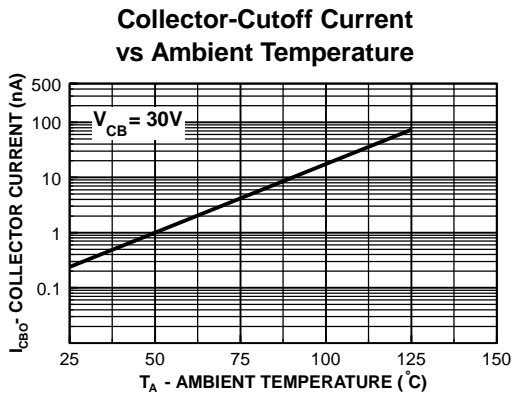
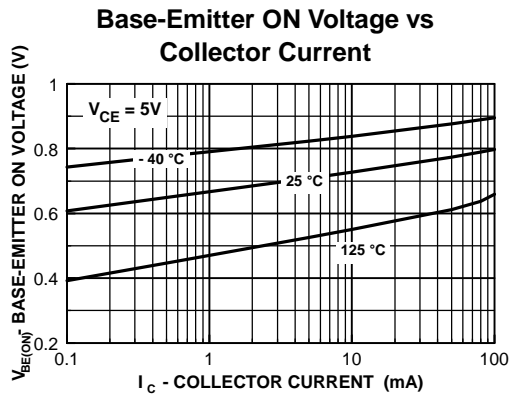
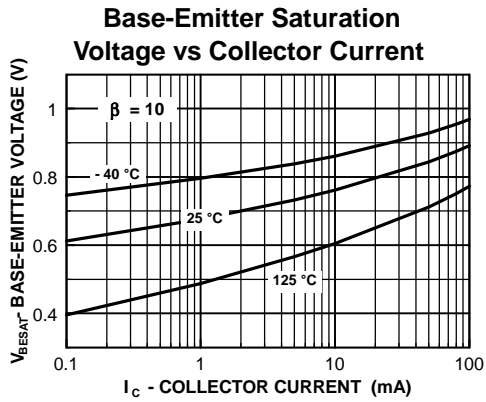
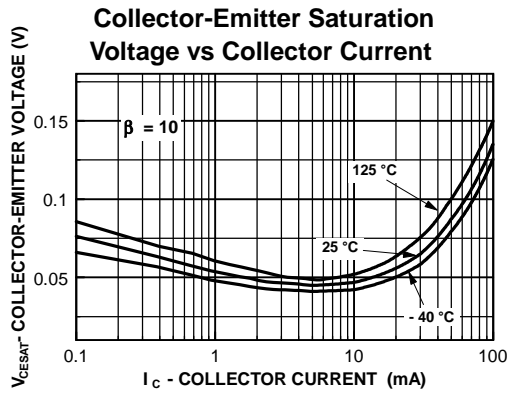
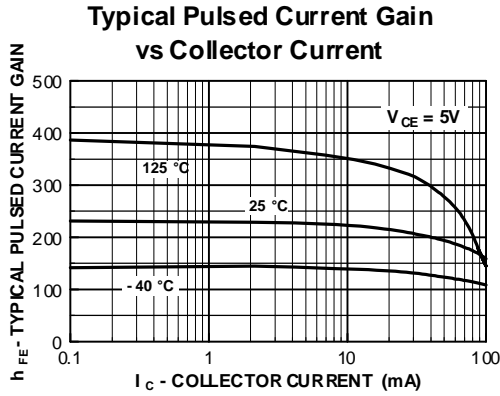
\*Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Spice Model

NPN (Is=6.734f Xti=3 Eg=1.11 Vaf=74.03 Bf=416.4 Ne=1.259 Ise=6.734 Ikf=66.78m Xtb=1.5 Br=.7371 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=3.638p Mjc=.3085 Vjc=.75 Fc=.5 Cje=4.493p Mje=.2593 Vje=.75 Tr=239.5n Tf=301.2p Itf=.4 Vtf=4 Xtf=2 Rb=10)

2N3904 / MMBT3904 / PZT3904

Typical Characteristics



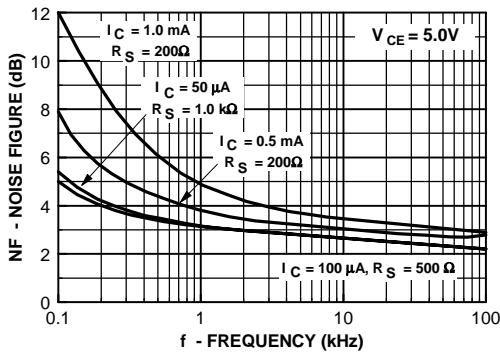
# NPN General Purpose Amplifier

(continued)

2N3904 / MMBT3904 / PZT3904

## Typical Characteristics (continued)

### Noise Figure vs Frequency



### Noise Figure vs Source Resistance



### Current Gain and Phase Angle vs Frequency



### Power Dissipation vs Ambient Temperature



### Turn-On Time vs Collector Current



### Rise Time vs Collector Current



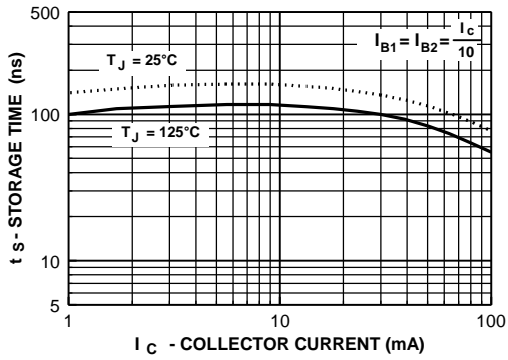
# NPN General Purpose Amplifier

(continued)

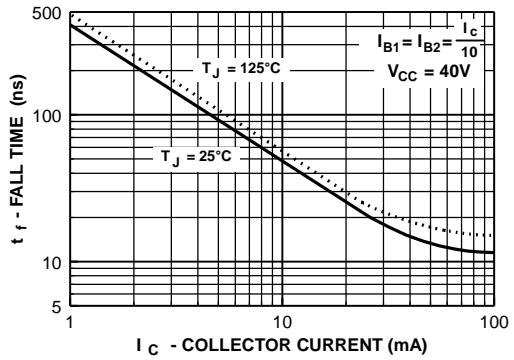
2N3904 / MMBT3904 / PZT3904

## Typical Characteristics (continued)

### Storage Time vs Collector Current



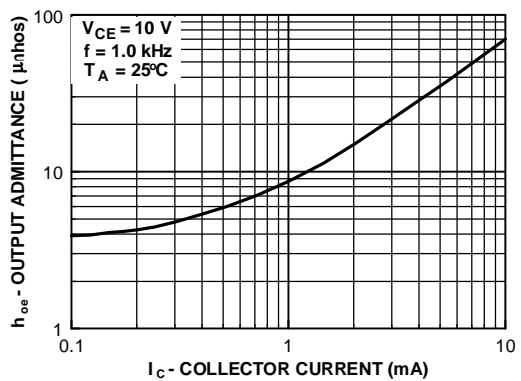
### Fall Time vs Collector Current



### Current Gain



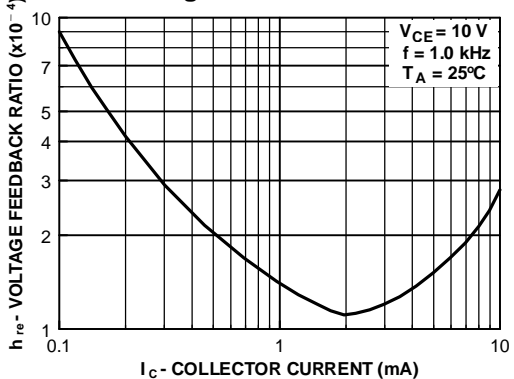
### Output Admittance



### Input Impedance



### Voltage Feedback Ratio



Test Circuits



FIGURE 1: Delay and Rise Time Equivalent Test Circuit



FIGURE 2: Storage and Fall Time Equivalent Test Circuit

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